

June 2014

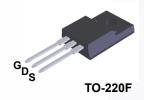
FQPF13N50CF N-Channel QFET® FRFET® MOSFET 500 V, 13 A, 540 m Ω

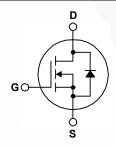
Features

- 13 A, 500 V, $R_{DS(on)}$ = 540 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.5 A
- Low Gate Charge (Typ. 43 nC)
- Low Crss (Typ. 20 pF)
- · 100% Avalanche Tested
- Fast Recovery Body Diode (Typ. 100 ns)

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FQPF13N50CF	Unit
V _{DSS}	Drain to Source Voltag	ge		500	V
I _D	Denie Coment	- Continuous (T _C = 25°C)		13	Α
	Drain Current	- Continuous (T _C = 100°C)		8	А
I _{DM}	Drain Current	- Pulsed	(Note 1)	52	A
V_{GSS}	Gate to Source Voltage			± 30	V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	530	mJ
AR	Avalanche Current		(Note 1)	13	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	19.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns
P_{D}	Dower Dissinction	(T _C = 25°C)		48	W
	Power Dissipation	- Derate above 25°C		0.39	W/°C
Γ _J , Τ _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
Τ _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

^{*}Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQPF13N50CF	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.58	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5		

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQPF13N50CF FQPF13N50CF		TO-220F	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.5		V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V			10	μΑ
I _{DSS} Z		V _{DS} = 400 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	-	-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6.5 A		0.43	0.54	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 6.5 A		15		S
	c Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1580	2055	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		180	235	pF
C _{rss}	Reverse Transfer Capacitance			20	25	pF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time V _{DD} = 250 V, I _D = 13 A,			25	60	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time			130	270	ns
t _f	Turn-Off Fall Time	(Note 4)		100	210	ns
Q_g	Total Gate Charge	V _{DS} = 400 V, I _D = 13 A,	/	43	56	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V	/	7.5		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		18.5		nC
Drain-S	ource Diode Characteristics and	I Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				13	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				52	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 13 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 13 A,		100	160	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.35		μС

Notes

^{1.} Repetitive Rating : Pulse width limited by maximum junction temperature.

^{2.} L = 5.6 mH, I $_{AS}$ = 13 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.

 $^{3.~}I_{SD} \leq 13~A,~di/dt \leq 200~A/\mu s,~V_{DD} \leq BV_{DSS,}~starting~~T_J = 25^{\circ}C.$

Essentially independent of operating temperature.

Typical Characteristics

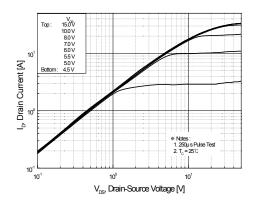


Figure 1. On-Region Characteristics

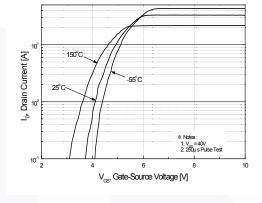


Figure 2. Transfer Characteristics

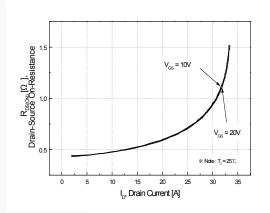


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

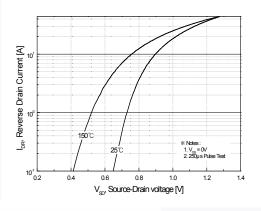


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

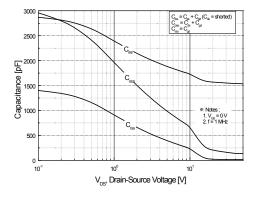


Figure 5. Capacitance Characteristics

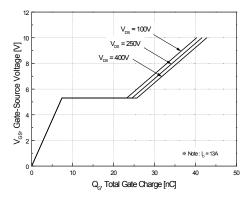


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

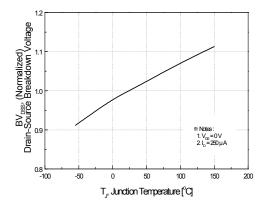


Figure 7. Breakdown Voltage Variation vs Temperature

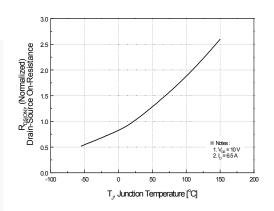


Figure 8. On-Resistance Variation vs Temperature

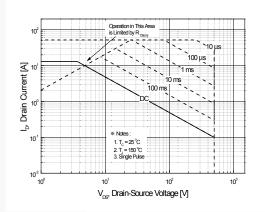


Figure 9. Maximum Safe Operating Area

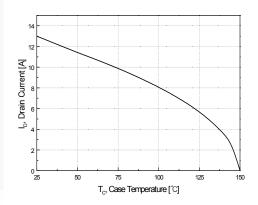


Figure 10. Maximum Drain Current vs Case Temperature

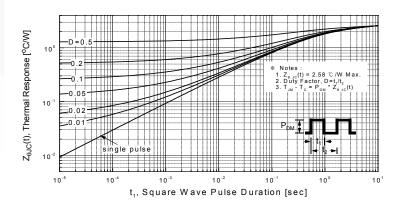


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

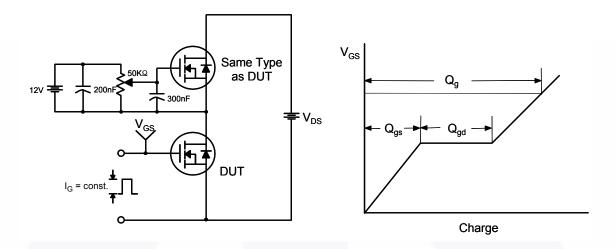


Figure 13. Resistive Switching Test Circuit & Waveforms

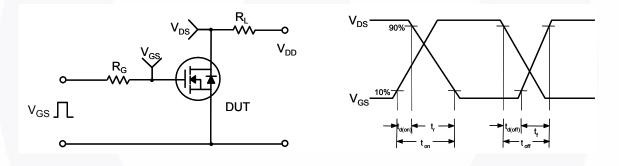
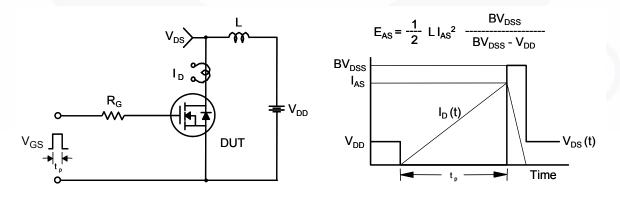


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



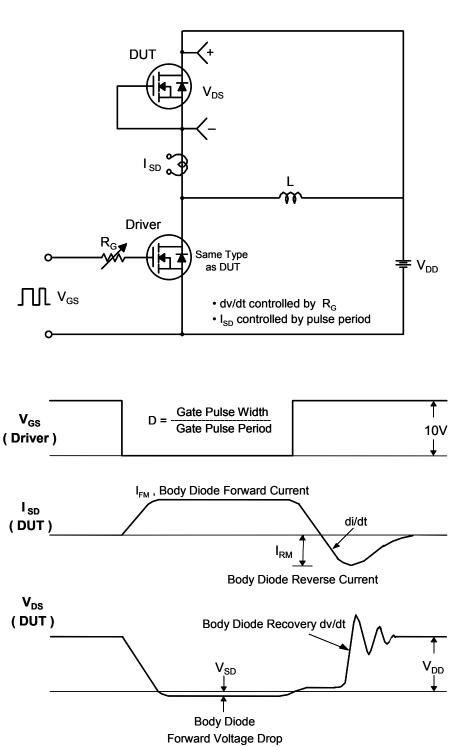


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

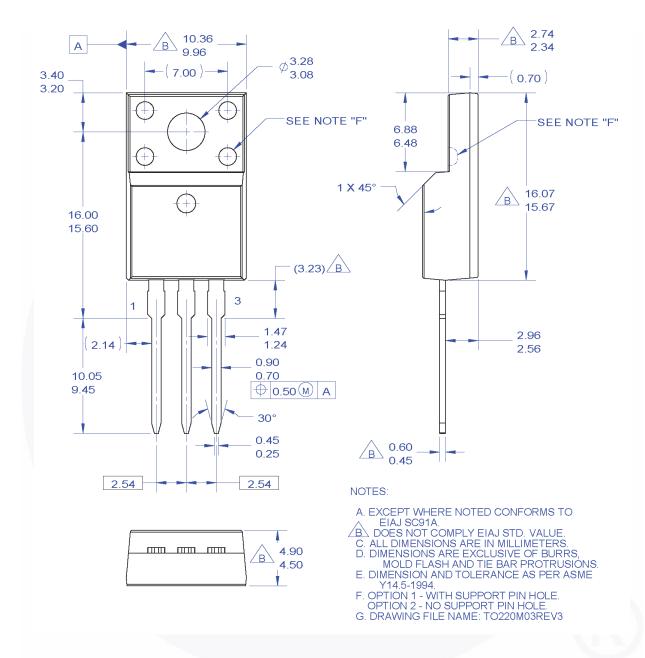


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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